



E. Compound Semiconductors 분과

2021년 1월 29일(금), 10:45-12:15 / 채널 C

[FC2-E] Compound Semiconductors IV

좌장: 차호영 교수 (홍익대학교)

<p>FC2-E-1 10:45-11:00</p>	<p>Normally-off Unidirectional Operation of p-GaN Gate AlGaIn/GaN Heterojunction Structure with Multi-Drain Electrode</p> <p>Tae-Hyeon Kim, Jun-Hyeok Yim, Won-Ho Jang, and Ho-Young Cha <i>School of Electronic and Electrical Engineering, Hongik University</i></p>
<p>FC2-E-2 11:00-11:15</p>	<p>Thin barrier AlGaIn/GaN HEMT 의 2DEG 특성 개선을 위한 AlN 박막 연구</p> <p>Won-Ho Jang, Jun-Hyeok Yim, Tea-Hyun Kim, and Ho-Young Cha <i>School of Electrical and Electronic Engineering, Hongik University</i></p>
<p>FC2-E-3 11:15-11:30</p>	<p>고온 질화 열처리 NO 가스 비에 따른 탄화규소 금속-산화막-반도체 계면 결함 제어 효과</p> <p>김인규^{1,2}, 김형우¹, 방욱¹, 양창현³, 강예환³, 윤승복³, 박기철², 문정현¹ ¹한국전기연구원 전력반도체연구센터, ²경상대학교 시스템 및 반도체공학과, ³에스파워테크닉스 연구소</p>
<p>FC2-E-4 11:30-11:45</p>	<p>Compact Modeling of Extrinsic Transconductance in InGaAs/InAlAs HEMTs</p> <p>Seung-Won Yun, Hyeon-Bhin Jo, Jun-Gyu Kim, and Dae-Hyun Kim <i>School of Electronic and Electrical Engineering, Kyungpook National University</i></p>
<p>FC2-E-5 11:45-12:00</p>	<p>Effects of Proton Irradiation on Current Characteristics of SiN-passivated AlGaIn/GaN MIS-HEMTs with TMAH-based Treatment Process</p> <p>Young Jun Yoon, Jae Sang Lee, and Dong-Seok Kim <i>Korea Multi-purpose Accelerator Complex, KAERI</i></p>
<p>FC2-E-6 12:00-12:15</p>	<p>Enhancement-mode β-Ga₂O₃ MOSFET 연구</p> <p>Chan-hee Jang, June-heang Choi, Gokhan Atmaca, and Ho-Young Cha <i>School of Electronic and Electrical Engineering, Hongik University</i></p>